N- and P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY		
	N-CHANNEL	P-CHANNEL
V_{DS} (V)	40	- 40
$R_{DS(on)}$ (Ω) at V_{GS} = ± 10 V	0.014	0.014
$R_{DS(on)}$ (Ω) at V_{GS} = ± 4.5 V	0.016	0.016
I_D (A)	50	- 50
Configuration	N- and P-Pair	

FEATURES

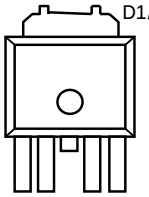
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested[d]

Pb-free
RoHS COMPLIANT
HALOGEN FREE

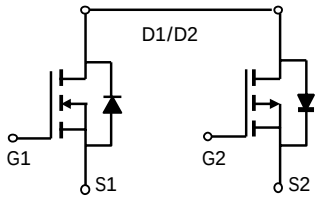
APPLICATIONS

- CCFL Inverter

TO-252-4L
D-PAK



Top View
Drain Connected to Tab



N-channel P-channel

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage		V_{DS}	40	- 40	V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current[a]	T_C = 25 °C	I_D	50	-50	A
	T_C = 125 °C		35	-35	
Continuous Source Current (Diode Conduction)[a]		I_S	50	-50	
Pulsed Drain Current[b]		I_{DM}	150	-150	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	30	- 30	
Single Pulse Avalanche Energy		E_{AS}	245	245	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	108	108	W
	T_C = 125 °C		32	32	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175		°C
Soldering Recommendations (Peak Temperature)			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	85	85	°C/W
Junction-to-Case (Drain)		R_{thJC}	3.1	3.1	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).
d. Parametric verification ongoing.

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)								
PARAMETER	**SYMBOL**	**TEST CONDITIONS**			**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static								
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		N-Ch	40	-	-	V
		V_{GS} = 0 V, I_D = - 250 µA		P-Ch	- 40	-	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		N-Ch	1.0	-	3.0	
		V_{DS} = V_{GS}, I_D = - 250 µA		P-Ch	- 1.0	-	-30	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		N-Ch	-	-	± 100	nA
				P-Ch	-	-	± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	N-Ch	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = - 40 V	P-Ch	-	-	- 1	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	N-Ch	-	-	50	
		V_{GS} = 0 V	V_{DS} = - 40 V, T_J = 125 °C	P-Ch	-	-	- 50	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	N-Ch	-	-	150	
		V_{GS} = 0 V	V_{DS} = - 40 V, T_J = 175 °C	P-Ch	-	-	- 150	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	N-Ch	25	-	-	A
		V_{GS} = - 10 V	V_{DS} ≤ 5 V	P-Ch	- 25	-	-	
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 38 A	N-Ch	-	0.014		Ω
		V_{GS} = - 10 V	I_D = - 38 A	P-Ch	-	0.014		
		V_{GS} = 10 V	I_D = 38 A, T_J = 125 °C	N-Ch	-	-	0.017	
		V_{GS} = - 10 V	I_D = - 38 A, T_J = 125 °C	P-Ch	-	-	0.017	
		V_{GS} = 10 V	I_D = 38 A, T_J = 175 °C	N-Ch	-	-	0.025	
		V_{GS} = - 10 V	I_D = - 38 A, T_J = 175 °C	P-Ch	-	-	0.025	
		V_{GS} = 4.5 V	I_D = 30 A	N-Ch	-	0.016	-	
		V_{GS} = - 4.5 V	I_D = - 30A	P-Ch	-	0.016	-	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 38 A		N-Ch	-	40	-	S
		V_{DS} = - 15 V, I_D = - 38 A		P-Ch	-	18	-	
Dynamic[b]								
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 20 V, f = 1 MHz	N-Ch	-	1799	2248	pF
		V_{GS} = 0 V	V_{DS} = - 20 V, f = 1 MHz	P-Ch	-	2000	3500	
Output Capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 20 V, f = 1 MHz	N-Ch	-	282	352	
		V_{GS} = 0 V	V_{DS} = - 20 V, f = 1 MHz	P-Ch	-	320	550	
Reverse Transfer Capacitance	C_{rss}	V_{GS} = 0 V	V_{DS} = 20 V, f = 1 MHz	N-Ch	-	109	136	
		V_{GS} = 0 V	V_{DS} = - 20 V, f = 1 MHz	P-Ch	-	220	360	
Total Gate Charge[c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 10 A	N-Ch	-	310	-	nC
		V_{GS} = - 10 V	V_{DS} = - 20 V, I_D = - 10 A	P-Ch	-	420	-	
Gate-Source Charge[c]	Q_{gs}	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 10 A	N-Ch	-	5.7	-	
		V_{GS} = - 10 V	V_{DS} = - 20 V, I_D = - 10 A	P-Ch	-	5.5	-	
Gate-Drain Charge[c]	Q_{gd}	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 10 A	N-Ch	-	4.8	-	
		V_{GS} = - 10 V	V_{DS} = - 20 V, I_D = - 10 A	P-Ch	-	10.5	-	
Gate Resistance	R_g	f = 1 MHz		N-Ch	2	4.11	6.2	Ω
				P-Ch	3.1	6.3	9.5	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

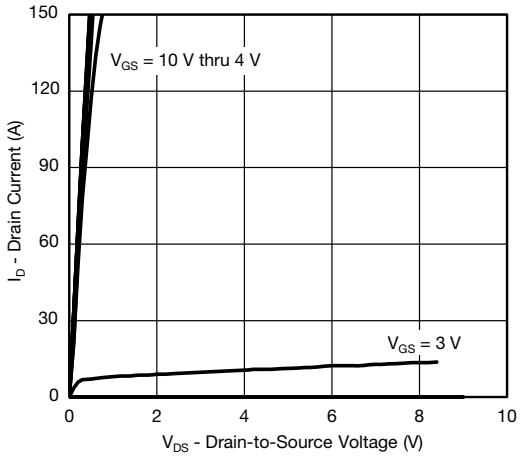
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 2 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch	-	7	11	ns
		V_{DD} = - 20 V, R_L = 2 Ω $I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω	P-Ch	-	11	17	
Rise Time[c]	t_r	V_{DD} = 20 V, R_L = 2 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch	-	21	32	
		V_{DD} = - 20 V, R_L = 2 Ω $I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω	P-Ch	-	9	14	
Turn-Off Delay Time[c]	$t_{d(off)}$	V_{DD} = 20 V, R_L = 2 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch	-	33	50	
		V_{DD} = - 20 V, R_L = 2 Ω $I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω	P-Ch	-	55	83	
Fall Time[c]	t_f	V_{DD} = 20 V, R_L = 2 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch	-	19	29	
		V_{DD} = - 20 V, R_L = 2 Ω $I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω	P-Ch	-	91	137	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}		N-Ch	-	-	32	A
			P-Ch	-	-	- 32	
Forward Voltage	V_{SD}	I_S = 4 A	N-Ch	-	0.79	1.2	V
		I_S = - 4 A	P-Ch	-	- 0.82	- 1.2	

Notes

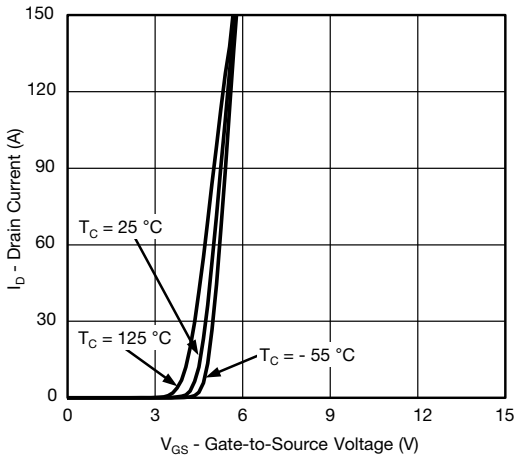
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

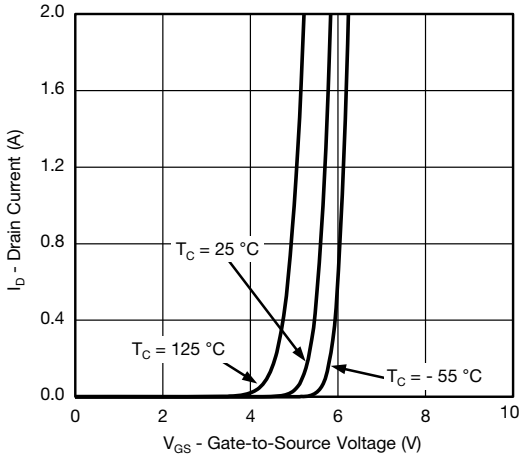
N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



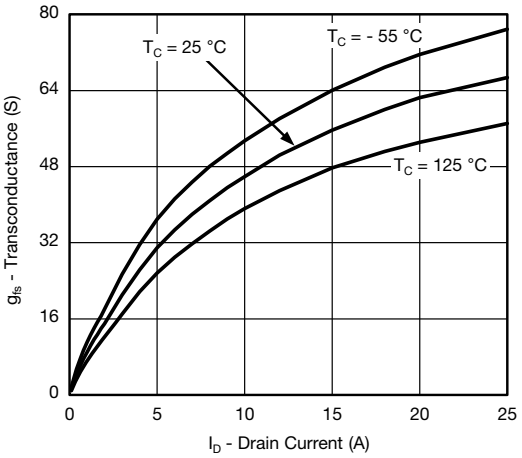
Output Characteristics



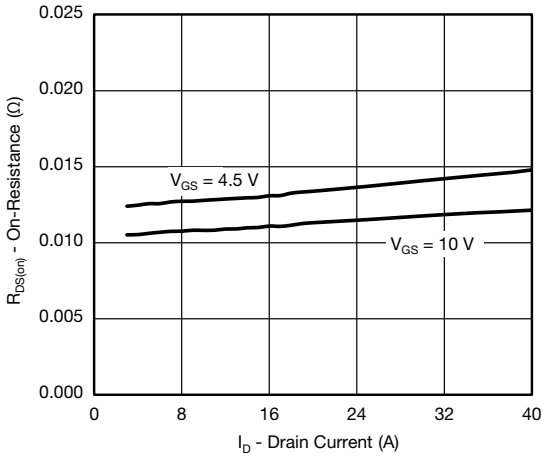
Transfer Characteristics



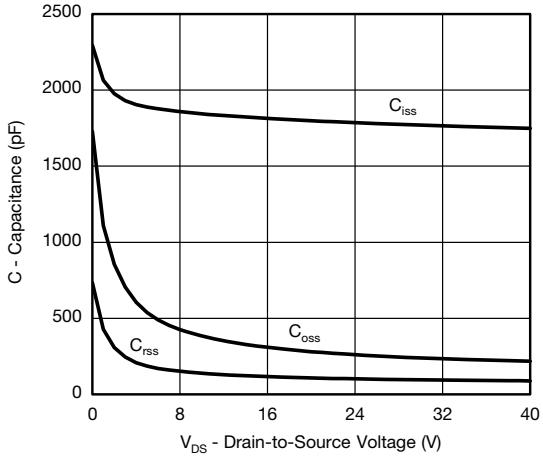
Transfer Characteristics



Transconductance

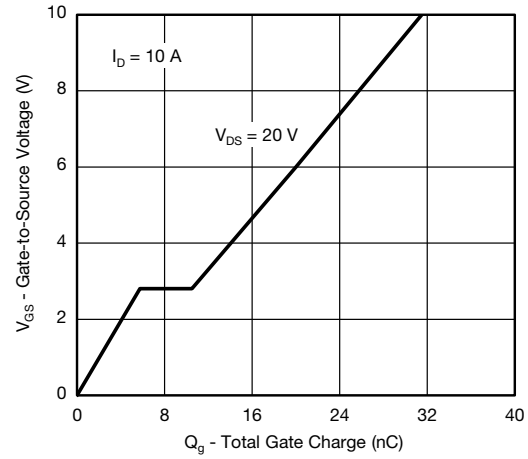


On-Resistance vs. Drain Current

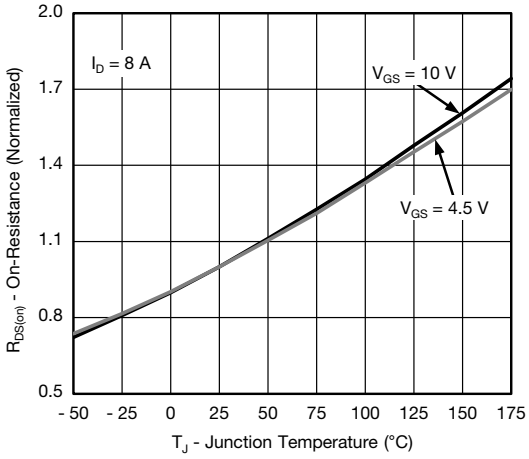


Capacitance

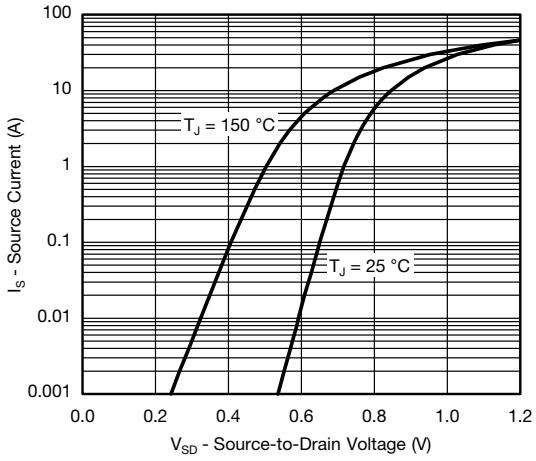
N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



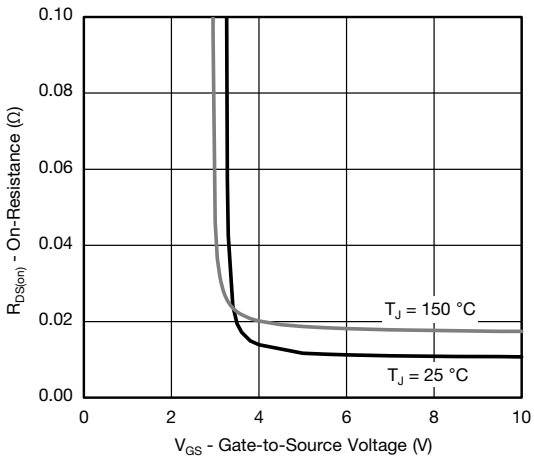
Gate Charge



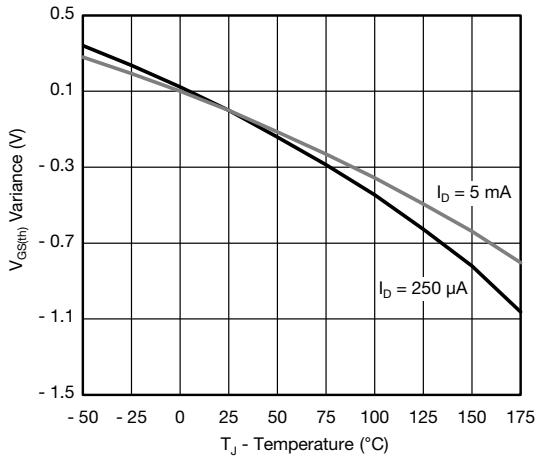
On-Resistance vs. Junction Temperature



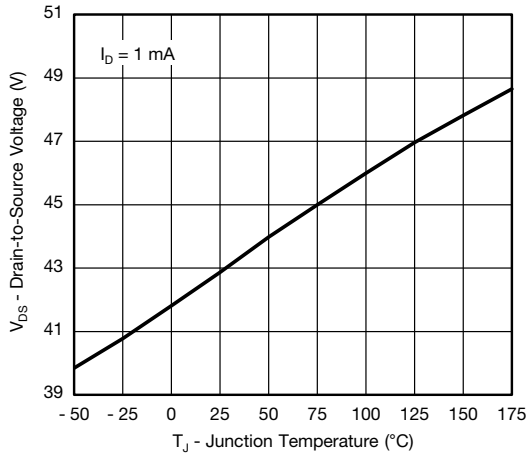
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

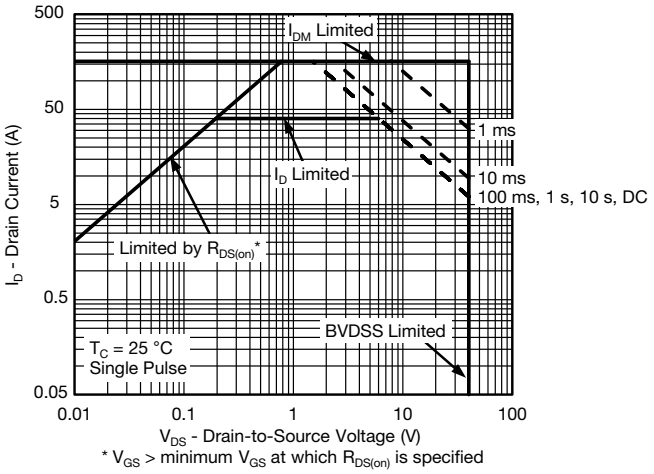


Threshold Voltage

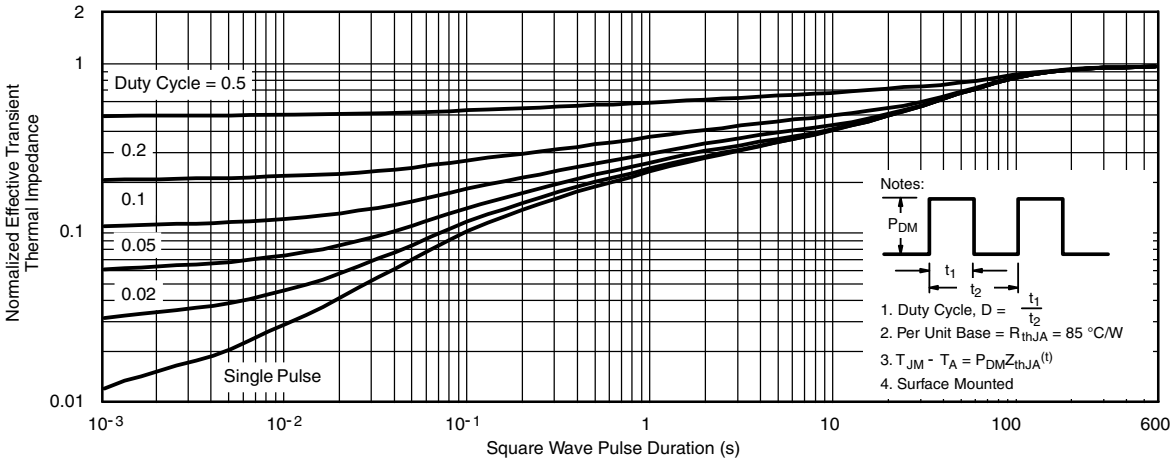


Drain Source Breakdown vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

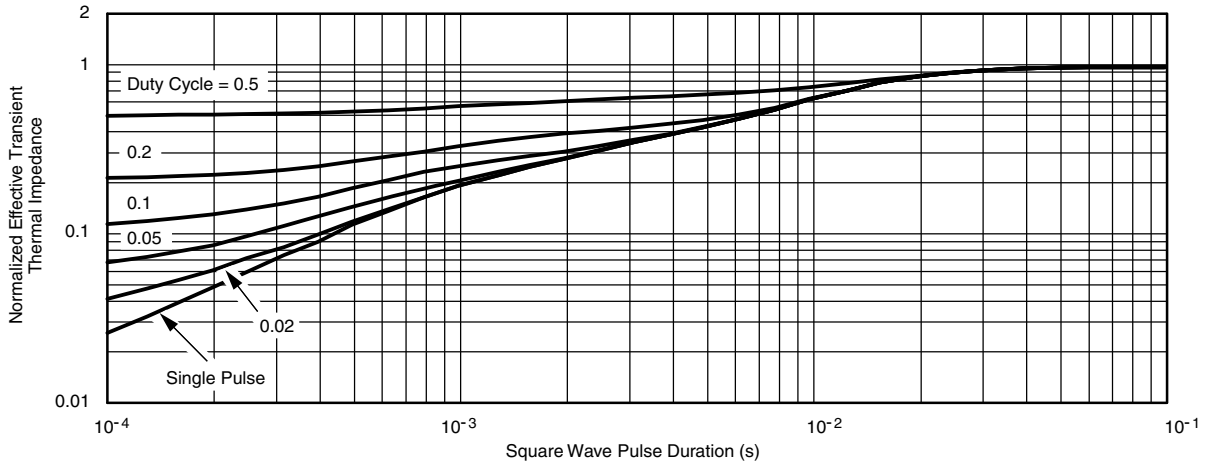


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



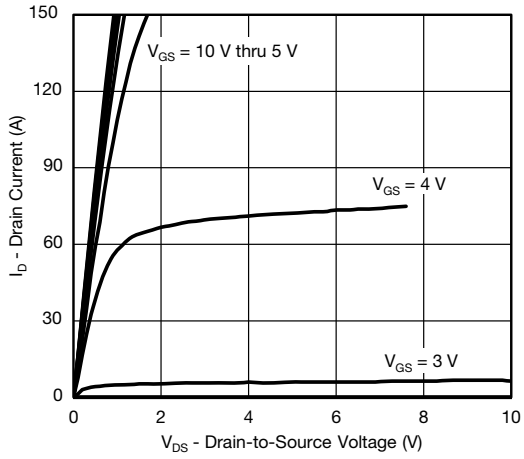
Normalized Thermal Transient Impedance, Junction-to-Case

Note

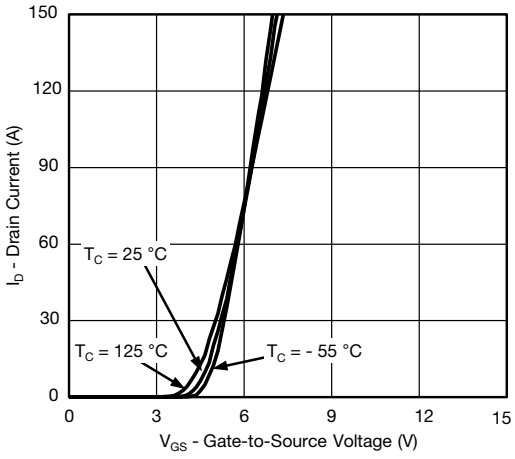
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

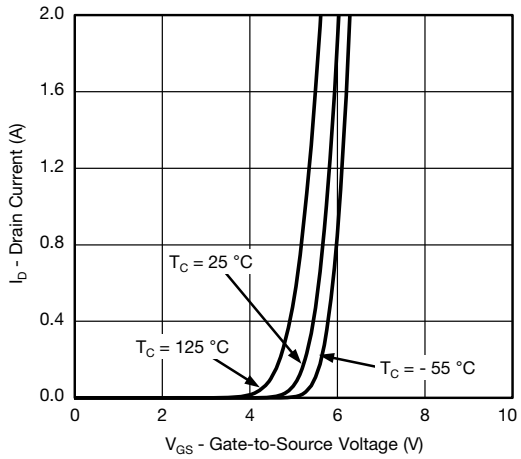
P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



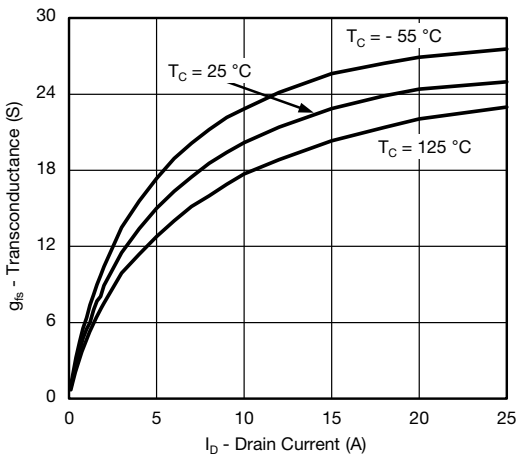
Output Characteristics



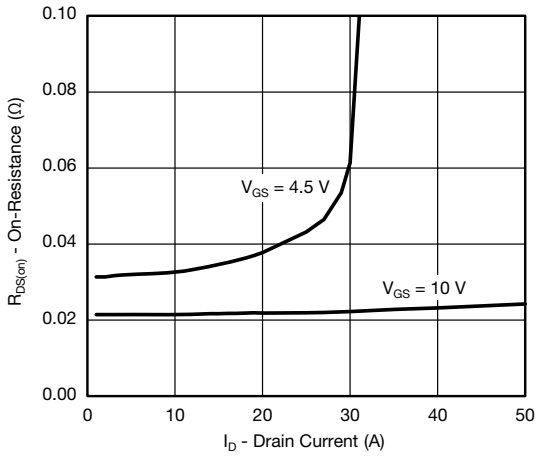
Transfer Characteristics



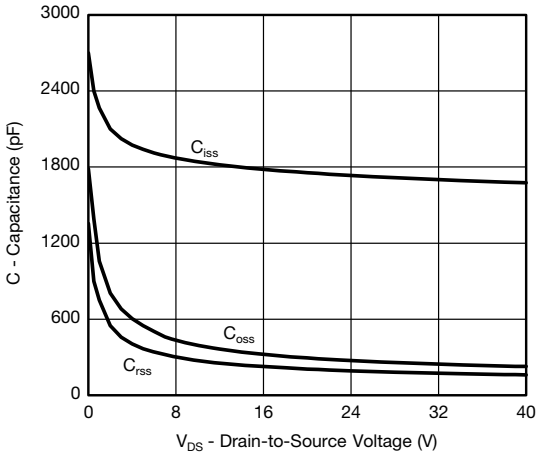
Transfer Characteristics



Transconductance

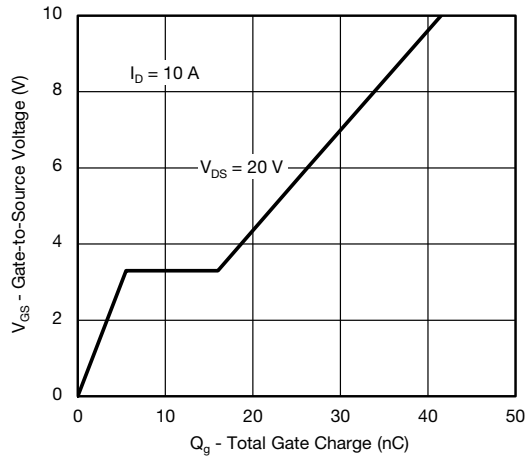


On-Resistance vs. Drain Current

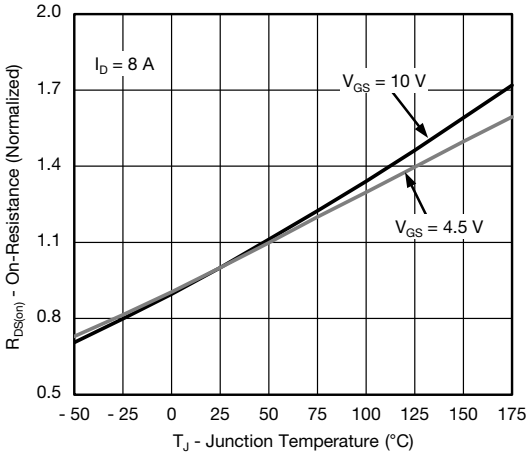


Capacitance

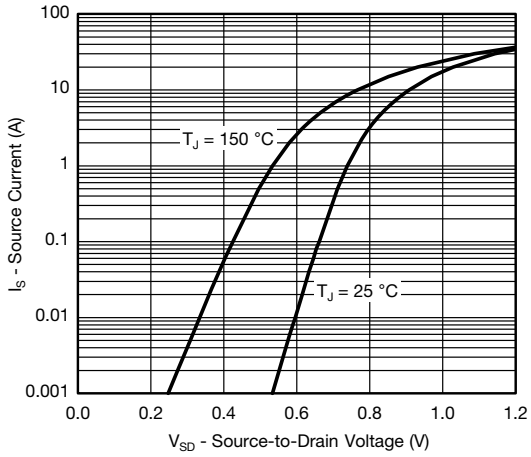
P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



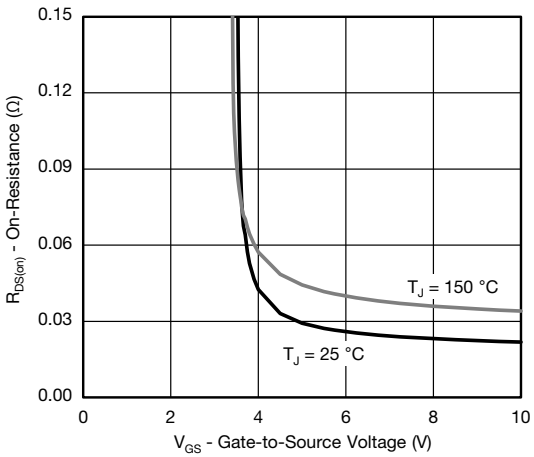
Gate Charge



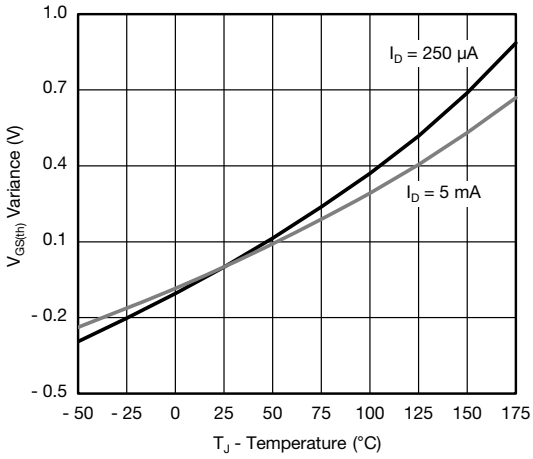
On-Resistance vs. Junction Temperature



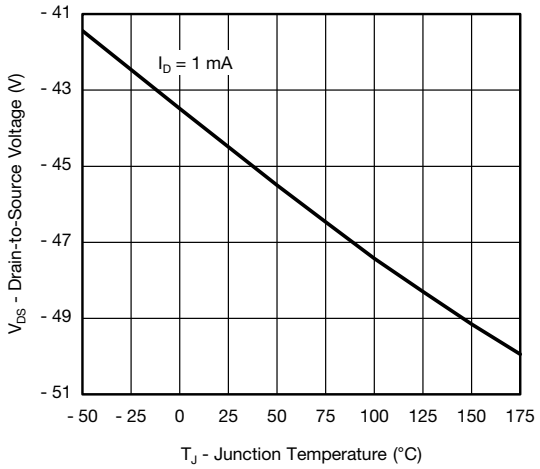
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

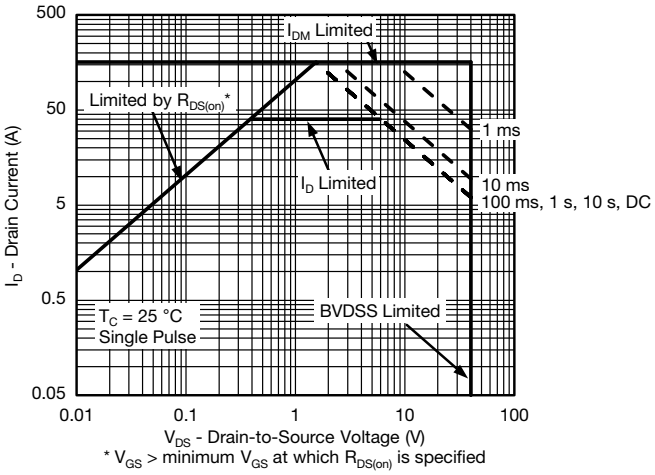


Threshold Voltage

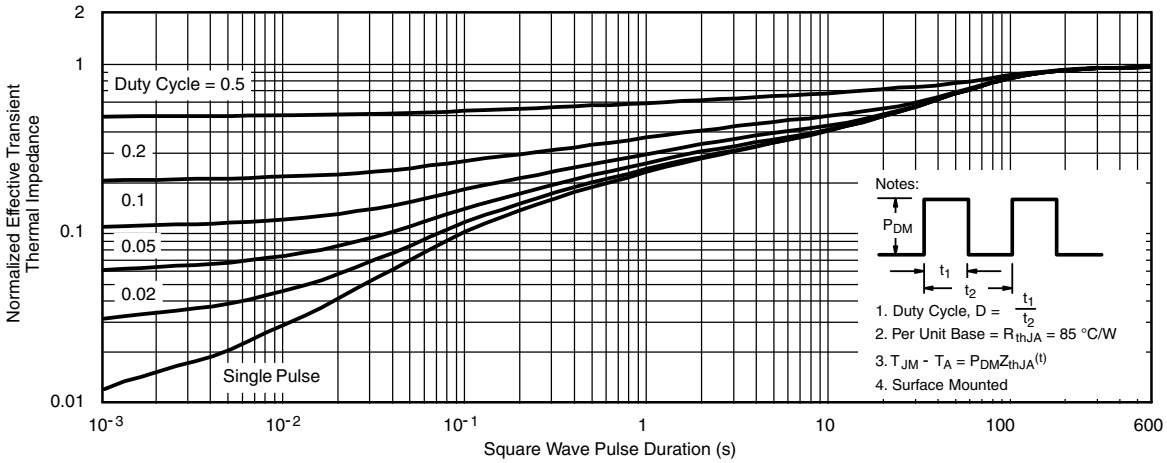


Drain Source Breakdown vs. Junction Temperature

P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

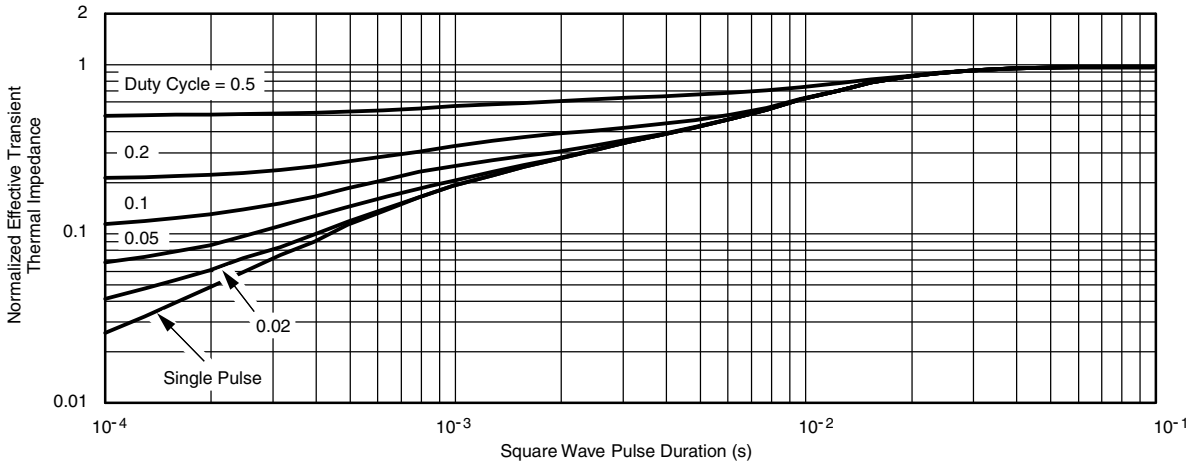


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



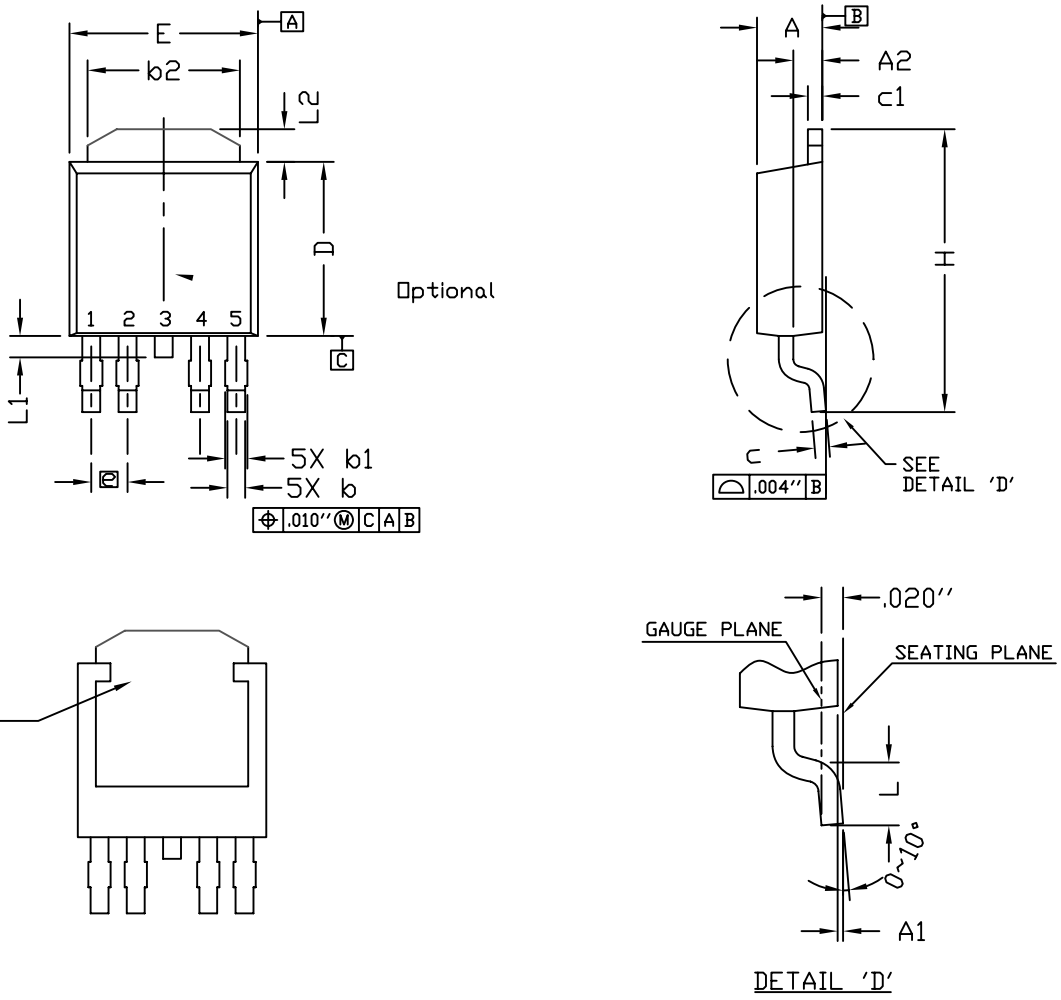
Normalized Thermal Transient Impedance, Junction-to-Case

Note

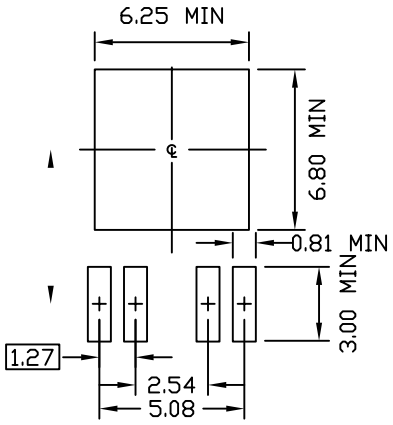
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-252_4L Package Outline



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOL	DIMENSION IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	2.184	2.286	2.388	0.086	0.090	0.094
A1	0.000	-----	0.127	0.000	-----	0.005
A2	0.889	-----	1.143	0.035	-----	0.045
b	0.508	-----	0.711	0.020	-----	0.028
b1	0.584	-----	0.787	0.023	-----	0.031
b2	4.953	-----	5.461	0.195	-----	0.215
c	0.457	0.508	0.610	0.018	0.020	0.024
c1	0.457	-----	0.610	0.018	-----	0.024
D	5.969	6.096	6.223	0.235	0.240	0.245
E	6.350	6.604	6.731	0.250	0.260	0.265
e	1.270 BSC.			0.050 BSC.		
H	9.398	-----	10.414	0.370	-----	0.410
L	1.270	-----	2.032	0.050	-----	0.080
L1	-----	-----	1.016	-----	-----	0.040
L2	0.889	-----	1.270	0.035	-----	0.050

NOTE
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MIL.
2. DIMENSION L IS MEASURED IN GAUGE PLANE.
3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED.
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
5. REFER TO JEDEC TO-252 (AD).

Disclaimer

All products due to improve reliability, function or design or for other reasons, product specifications and data are subject to change without notice.

Taiwan VBsemi Electronics Co., Ltd., branches, agents, employees, and all persons acting on its or their representatives (collectively, the "Taiwan VBsemi"), assumes no responsibility for any errors, inaccuracies or incomplete data contained in the table or any other any disclosure of any information related to the product.(www.VBsemi.com)

Taiwan VBsemi makes no guarantee, representation or warranty on the product for any particular purpose of any goods or continuous production. To the maximum extent permitted by applicable law on Taiwan VBsemi relinquished: (1) any application and all liability arising out of or use of any products; (2) any and all liability, including but not limited to special, consequential damages or incidental ; (3) any and all implied warranties, including a particular purpose, non-infringement and merchantability guarantee.

Statement on certain types of applications are based on knowledge of the product is often used in a typical application of the general product VBsemi Taiwan demand that the Taiwan VBsemi of. Statement on whether the product is suitable for a particular application is non-binding. It is the customer's responsibility to verify specific product features in the products described in the specification is appropriate for use in a particular application. Parameter data sheets and technical specifications can be provided may vary depending on the application and performance over time. All operating parameters, including typical parameters must be made by customer's technical experts validated for each customer application. Product specifications do not expand or modify Taiwan VBsemi purchasing terms and conditions, including but not limited to warranty herein.

Unless expressly stated in writing, Taiwan VBsemi products are not intended for use in medical, life saving, or life sustaining applications or any other application. Wherein VBsemi product failure could lead to personal injury or death, use or sale of products used in Taiwan VBsemi such applications using client did not express their own risk. Contact your authorized Taiwan VBsemi people who are related to product design applications and other terms and conditions in writing.

The information provided in this document and the company's products without a license, express or implied, by estoppel or otherwise, to any intellectual property rights granted to the VBsemi act or document. Product names and trademarks referred to herein are trademarks of their respective representatives will be all.

Material Category Policy

Taiwan VBsemi Electronics Co., Ltd., hereby certify that all of the products are determined to be oHS compliant and meets the definition of restrictions under Directive of the European Parliament 2011/65 / EU, 2011 Nian. 6. 8 Ri Yue restrict the use of certain hazardous substances in electrical and electronic equipment (EEE) - modification, unless otherwise specified as inconsistent.(www.VBsemi.com)

Please note that some documents may still refer to Taiwan VBsemi RoHS Directive 2002/95 / EC. We confirm that all products identified as consistent with the Directive 2002/95 / EC European Directive 2011/65 /.

Taiwan VBsemi Electronics Co., Ltd. hereby certify that all of its products comply identified as halogen-free halogen-free standards required by the JEDEC JS709A. Please note that some Taiwanese VBsemi documents still refer to the definition of IEC 61249-2-21, and we are sure that all products conform to confirm compliance with IEC 61249-2-21 standard level JS709A.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by VBsemi Elec ***manufacturer:***

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3